

## قائمة الاسئلة

## الأنظمه الكهر ميكانيكيه الدقيقه - قسم الهندسه الطبيه الحيويه- المستوى الرابع - درجة هذا الاختبار (50) د. خليل الحطاب

1)	In or	der to obtain a high deposition rate for the material, the vapor pressure of the source material must be
		the background vacuum pressure.
	1)	+ Above
	2)	- Below
		- Equal
	4)	- All of answers are correct
2)	,	e case of microgripper with a comb-drive actuator, a drastic in required actuation voltage
		of number of pairs of electrodes.
		- Increase, increase
		- Reduction, reduction
		+ Reduction, increase
		- All of answers are incorrect
3)	Ther	mopiles are multiple thermocouples that are arranged in with voltage output in
		Parallel, series
		- Series, parallel
		- Series, series
	,	- Parallel, parallel
1)		of the micro accelerometer are built on the principle of
_		- Electrostatic force
	,	- Electromagnetic force
	3)	- Thermal force
	4)	+ Mechanical deformation
5)	"Can	not maintain the actuated movement for sustained period of time due to overheating" this is a major
	disad	vantages of actuation techniques
	1)	- Thermal force
	2)	- Shape-memory alloys
	3)	+ Piezoelectric
	4)	- Electrostatic force
5)	The p	photoresist that after exposer to light dissolve in development is the type.
	1)	+ Positive
	2)	- Negative
	3)	- Either positive or negative
	- /	- All of answers are incorrect
7)	Wet	oxidation of silicon is often preferred because of
	1)	- Lower cost
	,	- Beter quality of SiO2
	3)	+ Faster oxidation
	4)	- All of answers are correct
3)	The l	nigher the class number of the clean room is the cleaner room.
	1)	- True.
	/	+ False.
9)		sion process is an example of
	1)	- Pressure driving flow
		+ Entropy-driven transport
	3)	- Gradient induced flow



- 4) All of answers are incorrect
- 10) Diffusion that occurs when the doping concentration is lower than the intrinsic carrier concentration is called intrinsic diffusion.
  - 1) + True.
  - 2) False.
- In the case of \_\_\_\_\_\_, an additional filament in the chamber is used to increase the sputter rate by producing additional electrons.
  - 1) Reactive sputtering
  - 2) + Triode sputtering
  - 3) Magnetron sputtering
  - 4) All of answers are incorrect
- is (are) not a property of sputtering thin films.
  - 1) Dense films
  - 2) Smaller grain size
  - 3) Good adhesion
  - 4) + Directionality
- 13) Laminar flow of compressible fluid normally takes place with Reynold number in the range of .
  - 1) 0-10
  - 2) + 10-100
  - 3) 100-1000
  - 4) >1000
- 14) The angle between the orientation <100> to the (111) plane in a single silicon crystal cell is degree.
  - 1) + 54.74
  - 2) 30
  - 3) 67.2
  - 4) 75

15)

e the geometry and the dimensions of the inkjet inter head as presented in next Figure. For a printing obition of 600 dots per inch (DPI), and the ink objet is assumed to produce a dot with a fill inchaess of 1 µm on the paper. Assume that the link opplet fakes the shape of a sphere and the inkwell is any refilled after ejection. Determine the electric tage required to eject ad troplet of ink from an inkjet after head with a PZT piezoelectric crystal as a unpling mechanism. V —

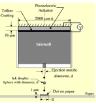


Table 7.14   Piezoelectric coefficients of	Coefficient d, 10 <sup>-12</sup> m/V	Electromechanical conversion factor K
	2.3	0.1
Ouertz (crystal SiO <sub>2</sub> )	100-190	0.49
Barlum titanate (BaTiO <sub>3</sub> ) Lead zirconate titanate, PZT (PbTi <sub>1 - x</sub> Zr <sub>x</sub> O <sub>3</sub> )	480	0.72
	250	
52rTiO <sub>6</sub>	80	
PNPiO*	350	0.78
Rochelle salt (NaKC <sub>4</sub> H <sub>4</sub> O <sub>6</sub> -4H <sub>2</sub> O) Polyinylidene fluoride, PVDF	18	ALCOHOLD STATE

- 1) 0.7435 v
- 2) + 0.9342 v
- 3) 1.5052 v
- 4) All of answers are incorrect
- 16) In general, phenomena that is weakly depends on size dominate in small dimensions is (are) \_\_\_\_\_.
  - 1) Friction
  - 2) Surface tension
  - 3) Diffusion
  - 4) + All of answers are correct
- 17) Extrinsic semiconductors are obtained from the intrinsic semiconductors by the process of . .

2 / 8 الصفحة

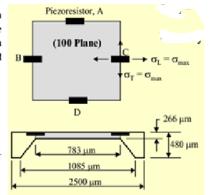


- 1) + Doping
- 2) Oxidation
- 3) Electroplating
- 4) Etching
- Estimate the change of resistance in a silicon piezo-resistance attached to the diaphragm of a pressure sensor as shown in the next Figure. If the Typical values of stress, and piezo-resistance coefficients:

$$\sigma_l = \sigma_T = \sigma_{max} = 186.8 \text{ MPa},$$

$$\pi_L = \pi_T = 0.02\pi_{44} \& \pi_{44} = 138.1 \times 10^{-11} \text{ pa}^{-1}$$

The change of resistance in a silicon piezo-resistance is



- 1) 1.21323
- 2) 2.51211
- + 0.01032
- 4) All of answers are incorrect
- 19) The single-unit cell for quartz contains \_\_\_\_\_ at the apexes at the base and \_\_\_\_ at the other apex of the tetrahedron.
  - 1) 2 oxygen atom, 3 silicon atoms
  - 2) 3 oxygen atoms, 2 silicon atoms
  - 3) 2 oxygen atoms, 2 silicon atoms
  - 4) + 3 oxygen atoms, 1 silicon atom
- A p-n junction refers to the location at which the implanted ion concentration \_\_\_\_\_ the existing background concentration of dopant in the wafer.
  - 1) Larger than
  - 2) Smaller than
  - 3) + Matches
  - 4) All of answers are incorrect
- 21) Electrophoresis is a common technique to separate macromolecules such as . .
  - 1) DNA
  - 2) RNA
  - 3) Proteins
  - 4) + All of answers are correct
- 22) The ability of a photoresist to produce acceptably sharp images is known as .
  - 1) Dose
  - 2) Resolution
  - 3) + Contrast
  - 4) Line of site
- 23) Electrohydrodynamic mainly focused on the fluid induced by electric fields.
  - 1) Dissolution
  - 2) + Motion
  - 3) Solidification
  - 4) All of answers are incorrect
- 24) The principal use of electrohydrodynamic in microsystems is to\_\_\_\_\_.
  - 1) Conduct electrolysis of minute chemicals

8 / 3 الصفحة



	2) +	Move minute amounts of fluid
	3) -	Detect minute amounts of fluid
	4) -	All of answers are incorrect
25)	Determi	ne the pressure required overcoming the surface tension of water in small tube of 0.5 mm inside
	diamete	r. Assume that the water is at 50oC. $\Delta P = $ Pa.
	1) -	773
	2) +	812
	3) -	855
	4) -	876
26)	The high	h throughput capabilities of capillary electrophoresis (CE) are achieved through the possibility of
	-	<u>-</u> •
		Reducing analysis time
		Lowering sample volume requirements
		Lowering solvent consumption
		Performing simultaneous separations in parallel channels
27)		mplementation within an electric field, the is used to separate charged from neutral particles.
	,	Deflection of beam
	2) -	
	3) -	Ci
	4) -	Optics system
28)		e a polymer electrically conductive, which of the following method is (are) not used?
		Pyrolysis
	,	Oxidation
	3) -	Doping
	4) -	1 2
29)		l number of atoms in a silicon unit crystal structure is
	/	12
	/	14
	,	16
	/	18
30)		rage distance a gas molecule travels before colliding with another gas molecule or the container walls
		n as
		Mean Free time
	2) -	Straggle
	3) -	Dose
	4) +	Mean Free Path
31)		ect of surface tension on fluid flowing in a capillary tube makes the volumetric flow the
		ow in mesosize tube.
	1) -	Much greater than
	2) -	About equal to
	3) +	
2.2	4) -	All of answers are incorrect
32)	_	wth of silicon crystals is slowest in thedirection.
	1) -	<100>
	2) -	<110>
	3) +	<111>
223	4) -	All of answers are incorrect
33)		r-pressure chemical vapor deposition (LPCVD) process is carried out at
	1) -	Ultra-High Vacuum

4 / 8 الصفحة



	2) - High Vacuum
	3) + Rough Vacuum
	4) - All of answers are correct
34)	In Clean Room Class I, the number of 0.5 μm particles per ft2 is
	1) + 1
	2) - 10
	3) - 100
	4) - 1000
35)	A silicon substrate is doped with phosphor ions at 30 keV. Assume the maximum concentration after the doped is 30 x $10^{18}$ /cm <sup>3</sup> . Hint: $R_p = 42x10^{-9}$ m, and $\Delta R_p = 19.5x10^{-9}$ m. The dose, Q is atoms/cm <sup>2</sup> .
	1.466 x 10 <sup>14</sup>
	2) - 50.22 x 10 <sup>12</sup>
	76.32 x 10 <sup>10</sup>
36)	4) - All of answers are correct  The secondary flats are used to indicate the, whereas the primary flats are used to indicate the
50)	
	1) - Crystal orientation of the wafer structure, Dopant type of the wafer
	2) + Dopant type of the wafer, Crystal orientation of the wafer structure
	3) - n-type, p-type
	4) - All answers are incorrect
37)	Laminar fluid flow means a .
.,	1) - High inertial forces
	2) - Low velocity
	3) - High Re
	4) + High velocity
38)	Electro-osmatic flow is a type of
50)	1) - Shear flow
	2) + Uniform flow
	3) - Parabolic flow
	4) - All of answers are incorrect
39)	In general, a microsystem consists of components.
37)	1) - One
	2) - Two
	3) + Three
	4) - Four
40)	Ion implementation is a technique to do:
- )	1) - Deposit an insulation layer

8 / 5 الصفحة



	2)	+	Dope a semiconductor		
	3)	-	Deposit a metallic layer		
	4)	-	Deposit a metallic layer on an insulator		
41)	Fo	or the t	hermal evaporation process, collision is less likely when Knudsen numbers, Kn		
	1)	-	Equal to 1		
	2)	-	<1		
	3)	+	>1		
	4)	-	All of answers are correct		
42)	W	ithin N	Molecular Beam Epitaxy (MBE), it is not possible to have a thin, sharp, box-shaped distribution of		
	do	pants.			
	1)	-	True.		
	2)	+	False.		
43)	Tl	ne line	-of-sight nature of the evaporation deposition process leads to the issue of for		
	to	pograp	shic features on a wafer.		
	1)	-	Sputtering yield		
	2)	+	Step coverage		
	3)	-	Shadowing		
	4)	-	All answers are correct		
44)	_		is the amount of material incident on a surface per unit surface area per unit time.		
	1)	-	Sputtering yield		
	2)	-	Step coverage		
	3)	-	Flux		
	4)	+	Arrival rate		
45)	There are piezoresistive coefficient in silicon piezoresistors.				
	1)	+	Three		
	2)	-	Four		
	3)	-	Five		
	4)	-	Six		
46)	Tl	ne num	ber of target atoms that are emitted per incident ion is called the		
	1)	-	Arrival rate		
	2)	-	Mean free path		
	3)	-			
	4)		Sputtering yield		
47)	W		f the following PVD technique can deposit film with better purity?		
	1)	+	E-beam evaporation		
	2)	-			
	3)	-	Thermal evaporation		
	4)	-	Thermal oxidation		
48)	A	hexan	nethyl disilazane (HMDS) is a(an)		
	1)	-			
	2)	+	Adhesion promoter		
	3)	-	Positive resist		
	4)_	-	All answers are correct		
49)			involves the growth of films over a substrate made of the same material.		
	1)	+	Single-crystal		
	2)	-	Organic		
	3)	-	Metallic		
<b>=</b> 0`	4)	-	Inorganic		
50)	In	LPCV	TD, at lower pressure, if mass transfer co-efficient is increased, the system operation switches to		

8 / 6 الصفحة



	ıne_		·	
	1)	+ Su	Surface reaction-controlled regime	
	2)	- M	Mass transport limited regime	
	3)	- D	Diffusion limited regime	
	4)	- Lo	Lower rate of deposition	
51)		mic	icromachining is primarily a subtractive process, while	micromachining is an additive
	pro	cess, bot	oth of which are used to fabricate MEMS devices.	
	1) _		Granular, achondritic	
	2)		Bulk, surface	
	3)		Reduction, oxidation	
	4)		Integrated, discrete	
52)			ass to silicon wafer can be done by	
	1)		Plasma Bonding	
	2)		Anodic Bonding	
	3)		Fusion bonding	
\	4)		Eutectic Bonding	
53)			ne MFP is of a lower order of magnitude than the distance f	rom the source to the substrate.
	1)		Γrue.	
- 1)	2)		False .	
54)			that exhibit electric polarization when exposed to intense el	ectric field are known as
	1)		Piezoelectric materials	
	2)		Ferromagnetic materials	
	3)		Electromagnetic materials Ferroelectric materials	
55)	4)		s reduction in electrode linear dimensions will gives a 1000	times reduction in the magnitude of
)))			ic forces.	times reduction in the magnitude of
	1)		Frue.	
	2)		False .	
56)			output of any sensor with respect to change in input is exp	ressed as
,0,	1)	_	Accuracy	
	2)		Sensitivity	
	3)		Γhreshold limit	
	4)		Resolution	
57)	-		bio sensor is wide used for	
	1)	-	Blood detection	
	2)	+ D	DNA detection	
	3)	- E	ECG detection	
	4)	- El	EMG detection	
58)	CN	T stand	d for	
	1)	- C	Copper Nano Tube	
	2)	+ C	Carbon Nano Tube	
	3)	- C	Cell Nano Tube	
	4)	- C	Crystal Nanotube	
59)	The	float zo	zone technique is used when a required to prod	luce the single-crystal substrates used in
	mic	roelectr	tronics and MEMS.	
	1)		Very high purity silicon substrate	
	2)		GaAs substrate	
	3)		Uniform distribution of dopants in silicon substrate	
	4)	- A	All answers are correct	

8 / 7 الصفحة



1)

2)

- True . + False .

60)	In piezoresistive sensors and force sensors, maximum displacement and stress of the square membrane occur			
	re	spectiv	vely at	
	1)	+	The center and edges	
	2)	-	The edges and center	
	3)	-	Displacement and stress remain uniform	
	4)	-	It cannot be predicted	
61)	_		_of the beam is inversely proportional to the of the beam.	
	1)	-	Stiffness, slope	
	2)	-	Stress, support reaction	
	3)	+	Stiffness, deflection	
	4)	-	Length, load	
62) Molecules that form hydrogen bonds with water molecules are hydrophob		[olecul	es that form hydrogen bonds with water molecules are hydrophobic.	
	1)	-	True.	
	2)	+	False.	
63)	St	tragglii	ng means that the ions with same macroscopic parameters penetrating a solid stop at the same depth.	
	1)	-	True.	
	2)	+	False.	
64)	In	a com	ab-drive, the combs are arranged so that they usually touched.	
	1)	-	True.	
	2)	+	False.	
65)	In	semic	onductors, the changes in geometry is the dominate resistance changes upon deformation.	